

# Harri Lipsanen

## List of Publications by Year in descending order

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405  
papers

8,264  
citations

61984

43  
h-index

74163

75  
g-index

408  
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408  
docs citations

408  
times ranked

9549  
citing authors

#	ARTICLE	IF	CITATIONS
1	Probing Electronic States in Monolayer Semiconductors through Static and Transient Third-Harmonic Spectroscopies. <i>Advanced Materials</i> , 2022, 34, e2107104.	21.0	10
2	Enhanced terahertz emission from mushroom-shaped InAs nanowire network induced by linear and nonlinear optical effects. <i>Nanotechnology</i> , 2022, 33, 085207.	2.6	4
3	Femtosecond Mode-Locked Yb:KYW Laser Based on InP Nanowire Saturable Absorber. <i>IEEE Photonics Technology Letters</i> , 2022, 34, 247-250.	2.5	5
4	InSb Nanowire Direct Growth on Plastic for Monolithic Flexible Device Fabrication. <i>ACS Applied Electronic Materials</i> , 2022, 4, 539-545.	4.3	1
5	WITio: A MATLAB data evaluation toolbox to script broader insights into big data from WITec microscopes. <i>SoftwareX</i> , 2022, 18, 101009.	2.6	2
6	Direct GaAs Nanowire Growth and Monolithic Light-Emitting Diode Fabrication on Flexible Plastic Substrates. <i>Advanced Photonics Research</i> , 2022, 3, .	3.6	4
7	Engineering the Dipole Orientation and Symmetry Breaking with Mixed-Dimensional Heterostructures. <i>Advanced Science</i> , 2022, 9, e2200082.	11.2	8
8	Designing outcoupling of light from nanostructured emitter in stratified medium with parasitic absorption. <i>Journal of Applied Physics</i> , 2022, 131, 223104.	2.5	0
9	Inducing Strong Light-Matter Coupling and Optical Anisotropy in Monolayer MoS <sub>2</sub> with High Refractive Index Nanowire. <i>ACS Applied Materials &amp; Interfaces</i> , 2022, 14, 31140-31147.	8.0	4
10	GaAs surface passivation for InAs/GaAs quantum dot based nanophotonic devices. <i>Nanotechnology</i> , 2021, 32, 130001.	2.6	7
11	Deterministic Modification of CVD Grown Monolayer MoS <sub>2</sub> with Optical Pulses. <i>Advanced Materials Interfaces</i> , 2021, 8, 2002119.	3.7	6
12	Symmetry Reduction in FEM Optics Modeling of Single and Periodic Nanostructures. <i>Symmetry</i> , 2021, 13, 752.	2.2	2
13	Applied electromagnetic optics simulations for nanophotonics. <i>Journal of Applied Physics</i> , 2021, 129, .	2.5	18
14	Optical Modification of Monolayer MoS <sub>2</sub> : Deterministic Modification of CVD Grown Monolayer MoS <sub>2</sub> with Optical Pulses (Adv. Mater. Interfaces 10/2021). <i>Advanced Materials Interfaces</i> , 2021, 8, 2170056.	3.7	0
15	All-parylene flexible wafer-scale graphene thin film transistor. <i>Applied Surface Science</i> , 2021, 551, 149410.	6.1	14
16	Graphene/Bi <sub>2</sub> Se <sub>3</sub> Heterojunction Phototransistor Using Photogating Effect Modulated by Tunable Tunneling Resistance. , 2021, , .		1
17	Effect of crystal structure on the Young's modulus of GaP nanowires. <i>Nanotechnology</i> , 2021, 32, 385706.	2.6	4
18	Giant All-Optical Modulation of Second-Harmonic Generation Mediated by Dark Excitons. <i>ACS Photonics</i> , 2021, 8, 2320-2328.	6.6	11

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19	Ultrafast carrier dynamics and nonlinear optical response of InAsP nanowires. <i>Photonics Research</i> , 2021, 9, 1811.	7.0	5
20	Mechanical and optical properties of as-grown and thermally annealed titanium dioxide from titanium tetrachloride and water by atomic layer deposition. <i>Thin Solid Films</i> , 2021, 732, 138758.	1.8	17
21	Single-step chemical vapour deposition of anti-pyramid MoS <sub>2</sub> /WS <sub>2</sub> vertical heterostructures. <i>Nanoscale</i> , 2021, 13, 4537-4542.	5.6	17
22	Trends in Carbon, Oxygen, and Nitrogen Core in the X-ray Absorption Spectroscopy of Carbon Nanomaterials: A Guide for the Perplexed. <i>Journal of Physical Chemistry C</i> , 2021, 125, 973-988.	3.1	30
23	Multilayer MoTe <sub>2</sub> Field-Effect Transistor at High Temperatures. <i>Advanced Materials Interfaces</i> , 2021, 8, 2100950.	3.7	14
24	Tuning of Emission Wavelength of CaS:Eu by Addition of Oxygen Using Atomic Layer Deposition. <i>Materials</i> , 2021, 14, 5966.	2.9	2
25	Grass-like alumina coated window harnesses the full omnidirectional potential of black silicon photodiodes. <i>Applied Optics</i> , 2021, 60, 10415.	1.8	3
26	Optical amplification by surface-plasmon-resonant Au grating substrates: Monolayer MoS <sub>2</sub> with 170-fold second harmonic generation and 3-fold (off-resonance) Raman scattering. <i>Superlattices and Microstructures</i> , 2021, 160, 107077.	3.1	4
27	Tunable Quantum Tunneling through a Graphene/Bi <sub>2</sub> Se <sub>3</sub> Heterointerface for the Hybrid Photodetection Mechanism. <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 58927-58935.	8.0	10
28	Tailoring the longitudinal electric fields of high-order laser beams and their direct verification in three dimensions. <i>Optics Communications</i> , 2020, 459, 124894.	2.1	3
29	High performance complementary WS <sub>2</sub> devices with hybrid Gr/Ni contacts. <i>Nanoscale</i> , 2020, 12, 21280-21290.	5.6	27
30	Superhydrophobic Antireflection Coating on Glass Using Grass-like Alumina and Fluoropolymer. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 49957-49962.	8.0	51
31	Hybrid GaAs nanowire-polymer device on glass: Al-doped ZnO (AZO) as transparent conductive oxide for nanowire based photovoltaic applications. <i>Journal of Crystal Growth</i> , 2020, 548, 125840.	1.5	4
32	Review of fabrication methods of large-area transparent graphene electrodes for industry. <i>Frontiers of Optoelectronics</i> , 2020, 13, 91-113.	3.7	31
33	Fabrication-friendly polarization-sensitive plasmonic grating for optimal surface-enhanced Raman spectroscopy. <i>Journal of the European Optical Society-Rapid Publications</i> , 2020, 16, .	1.9	2
34	Nanowire Oligomer Waveguide Modes towards Reduced Lasing Threshold. <i>Materials</i> , 2020, 13, 5510.	2.9	2
35	Experimental Study and Simulation of the Spectral Characteristics of LED Heterostructures with an InAs Active Region. <i>Technical Physics Letters</i> , 2020, 46, 150-153.	0.7	2
36	Direct Growth of Light-Emitting III-V Nanowires on Flexible Plastic Substrates. <i>ACS Nano</i> , 2020, 14, 7484-7491.	14.6	24

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37	Management of light and scattering in InP NWs by dielectric polymer shell. <i>Nanotechnology</i> , 2020, 31, 384003.	2.6	3
38	Metalorganic vapor phase epitaxy of wurtzite InP nanowires on GaN. <i>Applied Physics Letters</i> , 2020, 116, 093101.	3.3	2
39	Geometry Tailoring of Emission from Semiconductor Nanowires and Nanocones. <i>Photonics</i> , 2020, 7, 23.	2.0	10
40	Production and processing of graphene and related materials. <i>2D Materials</i> , 2020, 7, 022001.	4.4	333
41	Photodegradation of surface passivated GaAs nanowires. <i>Journal of Physics: Conference Series</i> , 2020, 1461, 012002.	0.4	1
42	Comparison of absorption simulation in semiconductor nanowire and nanocone arrays with the Fourier modal method, the finite element method, and the finite-difference time-domain method. <i>Nano Express</i> , 2020, 1, 030034.	2.4	13
43	Erbium-doped hybrid waveguide amplifiers with net optical gain on a fully industrial 300 mm silicon nitride photonic platform. <i>Optics Express</i> , 2020, 28, 27919.	3.4	20
44	Nonlinear optical absorption properties of InP nanowires and applications as a saturable absorber. <i>Photonics Research</i> , 2020, 8, 1035.	7.0	10
45	Nanowire-assisted microcavity in a photonic crystal waveguide and the enabled high-efficiency optical frequency conversions. <i>Photonics Research</i> , 2020, 8, 1734.	7.0	1
46	InAs-Nanowire-Based Broadband Ultrafast Optical Switch. <i>Journal of Physical Chemistry Letters</i> , 2019, 10, 4429-4436.	4.6	18
47	Growth of GaAs nanowire-graphite nanoplatelet hybrid structures. <i>CrystEngComm</i> , 2019, 21, 6165-6172.	2.6	5
48	Absorption modeling with FMM, FEM and FDT. , 2019, , .		1
49	Enhanced Tunneling in a Hybrid of Single-Walled Carbon Nanotubes and Graphene. <i>ACS Nano</i> , 2019, 13, 11522-11529.	14.6	23
50	Ultra-high on-chip optical gain in erbium-based hybrid slot waveguides. <i>Nature Communications</i> , 2019, 10, 432.	12.8	100
51	Aluminum Nitride Transition Layer for Power Electronics Applications Grown by Plasma-Enhanced Atomic Layer Deposition. <i>Materials</i> , 2019, 12, 406.	2.9	17
52	High photoresponsivity and broadband photodetection with a band-engineered $\text{WSe}_2/\text{SnSe}_2$ heterostructure. <i>Nanoscale</i> , 2019, 11, 3240-3247.	5.6	84
53	Single-photon sources with quantum dots in III-V nanowires. <i>Nanophotonics</i> , 2019, 8, 747-769.	6.0	47
54	Determination of Young's Modulus of Wurtzite III-V Nanowires by the Methods of Scanning Probe Microscopy. <i>Journal of Surface Investigation</i> , 2019, 13, 53-55.	0.5	0

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55	Site-specific growth of oriented ZnO nanocrystal arrays. Beilstein Journal of Nanotechnology, 2019, 10, 274-280.	2.8	2
56	Low-Temperature Plasma-Enhanced Atomic Layer Deposition of SiO <sub>2</sub> Using Carbon Dioxide. Nanoscale Research Letters, 2019, 14, 55.	5.7	7
57	Light-emitting InAs nanowires grown by MOVPE directly on flexible plastic substrates. , 2019, , .		0
58	Thermal conductivity suppression in GaAs@AlAs core-shell nanowire arrays. Nanoscale, 2019, 11, 20507-20513.	5.6	9
59	Title is missing!. Chinese Optics Letters, 2019, 17, 062301.	2.9	2
60	Comparison of FMM, FEM and FDTD for Absorption Modeling of Nanostructured Solar Cells and Photodetectors. , 2019, , .		0
61	Enhanced optical properties of InP nanowires by conformal polymer coating. , 2019, , .		0
62	Surface potential response from GaP nanowires synthesized with mixed crystal phases. Journal of Physics: Conference Series, 2019, 1400, 044018.	0.4	0
63	Ultrafast Dynamics of Photoinduced Electron-Hole Plasma in Semiconductor Nanowires. Semiconductors, 2018, 52, 19-23.	0.5	0
64	III-V nanowires on black silicon and low-temperature growth of self-catalyzed rectangular InAs NWs. Scientific Reports, 2018, 8, 6410.	3.3	11
65	Effect of Surface Wear on Corrosion Protection of Steel by CrN Coatings Sealed with Atomic Layer Deposition. ACS Omega, 2018, 3, 1791-1800.	3.5	18
66	Atomic layer deposition of AlN from AlCl <sub>3</sub> using NH <sub>3</sub> and Ar/NH <sub>3</sub> plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	19
67	Tribological properties of thin films made by atomic layer deposition sliding against silicon. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	7
68	Lifetimes of the Vibrational States of DNA Molecules in Functionalized Complexes of Semiconductor Quantum Dots. Technical Physics Letters, 2018, 44, 70-72.	0.7	4
69	Nonlinear Optics with 2D Layered Materials. Advanced Materials, 2018, 30, e1705963.	21.0	485
70	Transfer and patterning of chemical vapor deposited graphene by a multifunctional polymer film. Applied Physics Letters, 2018, 112, .	3.3	7
71	New method for MBE growth of GaAs nanowires on silicon using colloidal Au nanoparticles. Nanotechnology, 2018, 29, 045602.	2.6	6
72	Optical Properties of Bulk Gallium Oxide Grown from the Melt. Reviews on Advanced Materials Science, 2018, 57, 97-103.	3.3	4

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73	Coherent Electron Transport in Metamaterials of Integrated Semiconductor Quantum Dots and Biomolecules for Medical Imaging Applications. , 2018, , .		0
74	A MoSe <sub>2</sub> /WSe <sub>2</sub> Heterojunction-Based Photodetector at Telecommunication Wavelengths. Advanced Functional Materials, 2018, 28, 1804388.	14.9	95
75	Influence of plasma parameters on the properties of ultrathin Al <sub>2</sub> O <sub>3</sub> films prepared by plasma enhanced atomic layer deposition below 100 Å°C for moisture barrier applications. Japanese Journal of Applied Physics, 2018, 57, 125502.	1.5	16
76	Optical harmonic generation in monolayer group-VI transition metal dichalcogenides. Physical Review B, 2018, 98, .	3.2	92
77	Wide-band black silicon™ with atomic layer deposited NbN. Nanotechnology, 2018, 29, 335303.	2.6	5
78	Active synchronization and modulation of fiber lasers with a graphene electro-optic modulator. Optics Letters, 2018, 43, 3497.	3.3	12
79	Nanowire network-based multifunctional all-optical logic gates. Science Advances, 2018, 4, eaar7954.	10.3	51
80	Identifying threading dislocation types in ammonothermally grown bulk $\pm$ -GaN by confocal Raman 3-D imaging of volumetric stress distribution. Journal of Crystal Growth, 2018, 499, 47-54.	1.5	12
81	Photoresponse of Graphene-Gated Graphene-GaSe Heterojunction Devices. ACS Applied Nano Materials, 2018, 1, 3895-3902.	5.0	23
82	Comparison of mechanical properties and composition of magnetron sputter and plasma enhanced atomic layer deposition aluminum nitride films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	10
83	Low-Power Continuous-Wave Second Harmonic Generation in Semiconductor Nanowires. Laser and Photonics Reviews, 2018, 12, 1800126.	8.7	6
84	Nonlinear Optics: Nonlinear Optics with 2D Layered Materials (Adv. Mater. 24/2018). Advanced Materials, 2018, 30, 1870172.	21.0	8
85	Demonstration of longitudinally polarized optical needles. Optics Express, 2018, 26, 27572.	3.4	29
86	Corrosion protection of steel with multilayer coatings: Improving the sealing properties of physical vapor deposition CrN coatings with Al <sub>2</sub> O <sub>3</sub> /TiO <sub>2</sub> atomic layer deposition nanolaminates. Thin Solid Films, 2017, 627, 59-68.	1.8	32
87	Rapid and Large-Area Characterization of Exfoliated Black Phosphorus Using Third-Harmonic Generation Microscopy. Journal of Physical Chemistry Letters, 2017, 8, 1343-1350.	4.6	68
88	Graphene actively Q-switched lasers. 2D Materials, 2017, 4, 025095.	4.4	34
89	Crystal quality of two-dimensional gallium telluride and gallium selenide using Raman fingerprint. AIP Advances, 2017, 7, .	1.3	43
90	Tailorable second-harmonic generation from an individual nanowire using spatially phase-shaped beams. Laser and Photonics Reviews, 2017, 11, 1600175.	8.7	23

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91	Direct transfer of wafer-scale graphene films. <i>2D Materials</i> , 2017, 4, 035004.	4.4	29
92	Young's Modulus of Wurtzite and Zinc Blende InP Nanowires. <i>Nano Letters</i> , 2017, 17, 3441-3446.	9.1	30
93	New Approach for Thickness Determination of Solution-Deposited Graphene Thin Films. <i>ACS Omega</i> , 2017, 2, 2630-2638.	3.5	8
94	Nanowire encapsulation with polymer for electrical isolation and enhanced optical properties. <i>Nano Research</i> , 2017, 10, 2657-2666.	10.4	16
95	Aluminum oxide/titanium dioxide nanolaminates grown by atomic layer deposition: Growth and mechanical properties. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2017, 35, .	2.1	38
96	Review Article: Recommended reading list of early publications on atomic layer deposition "Outcome of the "Virtual Project on the History of ALD". <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2017, 35, .	2.1	65
97	"V curve hysteresis induced by gate-free charging of GaAs nanowires' surface oxide. <i>Applied Physics Letters</i> , 2017, 111, 132104.	3.3	9
98	Ultra-strong nonlinear optical processes and trigonal warping in MoS2 layers. <i>Nature Communications</i> , 2017, 8, 893.	12.8	177
99	Versatile Water-Based Transfer of Large-Area Graphene Films onto Flexible Substrates. <i>MRS Advances</i> , 2017, 2, 3749-3754.	0.9	2
100	Probing the longitudinal electric field of Bessel beams using second-harmonic generation from nano-objects. <i>Journal of Optics (United Kingdom)</i> , 2017, 19, 084011.	2.2	3
101	Low temperature and high quality atomic layer deposition HfO <sub>2</sub> coatings. , 2017, , .		1
102	MBE growth of nanowires using colloidal Ag nanoparticles. <i>Journal of Physics: Conference Series</i> , 2017, 864, 012010.	0.4	2
103	Scaling of graphene field-effect transistors supported on hexagonal boron nitride: radio-frequency stability as a limiting factor. <i>Nanotechnology</i> , 2017, 28, 485203.	2.6	15
104	Optically excited THz generation from ordered arrays of GaAs nanowires. <i>Procedia Engineering</i> , 2017, 201, 100-104.	1.2	1
105	Spontaneous and stimulated emission in InAsSb-based LED heterostructures. <i>Infrared Physics and Technology</i> , 2017, 85, 246-250.	2.9	14
106	Electroluminescence of InAs/InAs(Sb)/InAsSbP LED heterostructures in the temperature range 4.2-300 K. <i>Semiconductors</i> , 2017, 51, 239-244.	0.5	5
107	Rapid visualization of grain boundaries in monolayer MoS2 by multiphoton microscopy. <i>Nature Communications</i> , 2017, 8, 15714.	12.8	120
108	Measurement of Nanowire Optical Modes Using Cross-Polarization Microscopy. <i>Scientific Reports</i> , 2017, 7, 17790.	3.3	6

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109	Fast dynamics of photoexcited electron-hole plasma in GaAs nanowires. , 2017, , .		0
110	Nonlinear imaging of nanostructures using beams with binary phase modulation. Optics Express, 2017, 25, 10441.	3.4	3
111	Nonlinear microscopy using cylindrical vector beams: Applications to three-dimensional imaging of nanostructures. Optics Express, 2017, 25, 12463.	3.4	26
112	Detection of Raman Scattering Spectra of High Spectral Resolution in Short Oligonucleotides: Compared with the Full-Length DNA Spectra. Herald of the Bauman Moscow State Technical University, Series Natural Sciences, 2017, , .	0.5	0
113	Growth and properties of self-catalyzed (In,Mn)As nanowires. Physica Status Solidi - Rapid Research Letters, 2016, 10, 554-557.	2.4	3
114	Tunable Graphene-GaSe Dual Heterojunction Device. Advanced Materials, 2016, 28, 1845-1852.	21.0	90
115	Direct measurement of elastic modulus of InP nanowires with Scanning Probe Microscopy in PeakForce QNM mode. Journal of Physics: Conference Series, 2016, 769, 012029.	0.4	3
116	Protective capping and surface passivation of III-V nanowires by atomic layer deposition. AIP Advances, 2016, 6, .	1.3	29
117	Surface passivation of GaAs nanowires by the atomic layer deposition of AlN. Semiconductors, 2016, 50, 1619-1621.	0.5	1
118	Structural and chemical analysis of annealed plasma-enhanced atomic layer deposition aluminum nitride films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	22
119	Second and third harmonic generation in few-layer gallium telluride characterized by multiphoton microscopy. Applied Physics Letters, 2016, 108, .	3.3	58
120	Resonant features of the terahertz generation in semiconductor nanowires. Semiconductors, 2016, 50, 1561-1565.	0.5	5
121	Efficient terahertz generation by ordered arrays of GaAs nanowires. , 2016, , .		1
122	Black phosphorus polycarbonate polymer composite for pulsed fibre lasers. Applied Materials Today, 2016, 4, 17-23.	4.3	87
123	Optical characterization of directly deposited graphene on a dielectric substrate. Optics Express, 2016, 24, 2965.	3.4	5
124	TEM study of defect structure of GaN epitaxial films grown on GaN/Al <sub>2</sub> O <sub>3</sub> substrates with buried column pattern. Journal of Crystal Growth, 2016, 445, 30-36.	1.5	5
125	Thermal conductivity of amorphous Al <sub>2</sub> O <sub>3</sub> /TiO <sub>2</sub> nanolaminates deposited by atomic layer deposition. Nanotechnology, 2016, 27, 445704.	2.6	27
126	Atomic Layer Engineering of Er-Ion Distribution in Highly Doped Er:Al <sub>2</sub> O <sub>3</sub> for Photoluminescence Enhancement. ACS Photonics, 2016, 3, 2040-2048.	6.6	27



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127	Lithography-free shell-substrate isolation for core-shell GaAs nanowires. Nanotechnology, 2016, 27, 275603.	2.6	1
128	Synthesis and properties of ultra-long InP nanowires on glass. Nanotechnology, 2016, 27, 505606.	2.6	7
129	Direct observation of confined acoustic phonon polarization branches in free-standing semiconductor nanowires. Nature Communications, 2016, 7, 13400.	12.8	71
130	Pyrolytic carbon coated black silicon. Scientific Reports, 2016, 6, 25922.	3.3	12
131	Integration of atomic layer deposited nanolaminates on silicon waveguides (Conference) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50		
132	Atomic layer deposition of highly doped Er:Al <sub>2</sub> O <sub>3</sub> and Tm:Al <sub>2</sub> O <sub>3</sub> for silicon-based waveguide amplifiers (Conference Presentation). , 2016, , .		0
133	Synchrotron X-ray diffraction topography study of bonding-induced strain in silicon-on-insulator wafers. Thin Solid Films, 2016, 603, 435-440.	1.8	2
134	Enhancement of the photoluminescence in Er-doped Al <sub>2</sub> O <sub>3</sub> fabricated by atomic layer deposition. , 2016, , .		1
135	A technique for large-area position-controlled growth of GaAs nanowire arrays. Nanotechnology, 2016, 27, 135601.	2.6	9
136	Direct comparison of second and third harmonic generation in mono- and few-layer MX <sub>2</sub> (M=Mo,W;) Tj ETQq0 0 0 rgBT /Overlock 10 Tf		
137	Influence of surface passivation on electric properties of individual GaAs nanowires studied by current-voltage AFM measurements. Lithuanian Journal of Physics, 2016, 56, .	0.4	11
138	Nonlinear microscopy of nano-objects using excitation beam profiles with engineered phase jumps. , 2016, , .		0
139	Spectral characteristics of mid-infrared light-emitting diodes based on InAs(Sb,P). Scientific and Technical Journal of Information Technologies, Mechanics and Optics, 2016, , 76-84.	0.2	1
140	Polarization and Thickness Dependent Absorption Properties of Black Phosphorus: New Saturable Absorber for Ultrafast Pulse Generation. Scientific Reports, 2015, 5, 15899.	3.3	268
141	Wafer-scale self-organized InP nanopillars with controlled orientation for photovoltaic devices. Nanotechnology, 2015, 26, 415304.	2.6	13
142	Generation of terahertz radiation in ordered arrays of GaAs nanowires. Applied Physics Letters, 2015, 106, .	3.3	21
143	Observation of linear I-V curves on vertical GaAs nanowires with atomic force microscope. Journal of Physics: Conference Series, 2015, 661, 012031.	0.4	3
144	Broadband laser polarization control with aligned carbon nanotubes. Nanoscale, 2015, 7, 11199-11205.	5.6	14

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145	A physics-based model of gate-tunable metal-graphene contact resistance benchmarked against experimental data. <i>2D Materials</i> , 2015, 2, 025006.	4.4	30
146	Investigation of Second- and Third-Harmonic Generation in Few-Layer Gallium Selenide by Multiphoton Microscopy. <i>Scientific Reports</i> , 2015, 5, 10334.	3.3	98
147	Second-Harmonic Generation Imaging of Semiconductor Nanowires with Focused Vector Beams. <i>Nano Letters</i> , 2015, 15, 1564-1569.	9.1	66
148	Fabrication of Dual-Type Nanowire Arrays on a Single Substrate. <i>Nano Letters</i> , 2015, 15, 1679-1683.	9.1	9
149	Processing and characterization of epitaxial GaAs radiation detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2015, 796, 51-55.	1.6	8
150	Solubility of Boron, Carbon, and Nitrogen in Transition Metals: Getting Insight into Trends from First-Principles Calculations. <i>Journal of Physical Chemistry Letters</i> , 2015, 6, 3263-3268.	4.6	50
151	Optical limiting in solutions of InP and GaAs nanowires and hybrid systems based on such nanocrystals. <i>Technical Physics Letters</i> , 2015, 41, 120-123.	0.7	3
152	All-Graphene Three-Terminal-Junction Field-Effect Devices as Rectifiers and Inverters. <i>ACS Nano</i> , 2015, 9, 5666-5674.	14.6	14
153	Slot waveguide ring resonators coated by an atomic layer deposited organic/inorganic nanolaminate. <i>Optics Express</i> , 2015, 23, 26940.	3.4	14
154	Nanotribological, nanomechanical and interfacial characterization of atomic layer deposited TiO <sub>2</sub> on a silicon substrate. <i>Wear</i> , 2015, 342-343, 270-278.	3.1	13
155	The effect of resonant Mie absorption under THz radiation emission in semiconductor nanowires. <i>Optics and Spectroscopy (English Translation of Optika i Spektroskopiya)</i> , 2015, 119, 754-758.	0.6	1
156	Observing grain boundaries in monolayer molybdenum disulphide by multiphoton microscopy. , 2015, , .		0
157	Resonant raman scattering in complexes of nc-Si/SiO <sub>2</sub> quantum dots and oligonucleotides. <i>Technical Physics Letters</i> , 2014, 40, 1035-1037.	0.7	2
158	Leakage currents of large area InP/InGaAs heterostructures. <i>Materials Research Society Symposia Proceedings</i> , 2014, 1635, 75-81.	0.1	0
159	Effects of Zn doping on GaAs nanowires. , 2014, , .		4
160	Impact of ALD grown passivation layers on silicon nitride based integrated optic devices for very-near-infrared wavelengths. <i>Optics Express</i> , 2014, 22, 5684.	3.4	24
161	Radiation detectors fabricated on high-purity GaAs epitaxial materials. <i>Journal of Instrumentation</i> , 2014, 9, C12024-C12024.	1.2	1
162	Stress distribution in GaN nanopillars using confocal Raman mapping technique. <i>Applied Physics Letters</i> , 2014, 104, 151906.	3.3	5

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163	Yield and leakage currents of large area lattice matched InP/InGaAs heterostructures. Journal of Applied Physics, 2014, 116, .	2.5	4
164	Strong surface passivation of GaAs nanowires with ultrathin InP and GaP capping layers. Applied Physics Letters, 2014, 105, .	3.3	31
165	Nanolaminate structures fabricated by ALD for reducing propagation losses and enhancing the third-order optical nonlinearities. Proceedings of SPIE, 2014, , .	0.8	6
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